Supertex inc.

VP0204N6 / VP0204N7
VP0206N6 / VP0206N7

T-43-25

P-Channel Enhancement-Mode Vertical DMOS Power FETs Quad Array

Ordering Information

BV_{DSS} / BV_{DGS}	$R_{DS(ON)}$ (max)	Order Number / Package	
		14-Pin P-Dip	14-Pin C-Dip*
-40V	4Ω	VP0204N6	VP0204N7
-60V	4Ω	VP0206N6	VP0206N7

*14-pin Side Brazed Ceramic Dip.

Features

- ☐ 4 independent channels
- ☐ 4 electrically isolated die
- ☐ Commercial and Military versions available
- ☐ Freedom from secondary breakdown
- ☐ Low power drive requirement
- ☐ Low C_{ISS} and fast switching speeds
- ☐ High input impedance and high gain

Applications

- ☐ Motor control
- ☐ Convertors
- ☐ Amplifiers
- ☐ Switches
- ☐ Power supply circuits
- ☐ Driver (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

Thermal Characteristics

Package		Plastic DIP	Ceramic DIP
I_D continuous & I_{DR} (single die)	N-Channel	0.6A	0.7A
	P-Channel		
I_D pulsed* & I_{DRM}*	N-Channel	2.5A	2.5A
	P-Channel		
Power Dissipation @ T_C = 25°C‡		3W	4W
θ_{ja} (°C/W)		83.3	62.5
θ_{jc} (°C/W)		41.6	31.2

* Pulse test 300 µS pulse, 2% duty cycle.
‡ Total for package.

Advanced DMOS Technology

These enhancement-mode (normally-off) power transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and negative temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

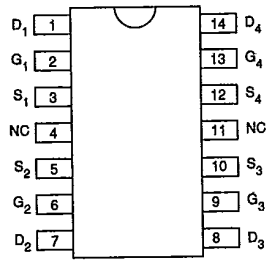
Supertex Vertical DMOS Power FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Electrical Characteristics

10

Refer to VP02A Data Sheet for detailed characteristics.

Pin Configuration



top view

14-pin DIP